Characterisation of 1200 V RB-IGBTs with different irradiation levels under hard and soft switching conditions

Blinov, Andrei; Korkh, Oleksandr; Vinnikov, Dmitri; Waind, Peter 2018 20th European Conference on Power Electronics and Applications (EPE'18 ECCE Europe) : Riga, Latvia, 17-21 September 2018 2018 / p. 1382-1391 : ill https://ieeexplore.ieee.org/document/8515535

Comparison of the power losses in 1700V Si IGBT and SiC MOSFET modules including reverse conduction [Electronic resource]

Rabkowski, Jacek; Platek, Tadeusz EPE'15 ECCE Europe : 8-10 September 2015, Geneva, Switzerland : 17th European Conference on Power Electronics and Applications 2015 / [10] p. : ill. [USB] <u>http://dx.doi.org/10.1109/EPE.2015.7309444</u>

Operation of Single-Chip MOSFET and IGBT Devices after failure due to repetitive avalanche [Electronic resource]

Blinov, Andrei; Norrga, Staffan; Tibola, Gabriel EPE'15 ECCE Europe : 8-10 September 2015, Geneva, Switzerland : 17th European Conference on Power Electronics and Applications 2015 / p. 1-9 : ill. [USB] <u>http://dx.doi.org/10.1109/EPE.2015.7309190</u>